

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Kittl et al.

Docket No.: TI-23892

Serial No: TBD

Examiner: TBD

Filed: 12/13/01

Art Unit: TBD

For: METHOD TO IMPROVE SILICIDE FORMATION ON POLYSILICON

PRELIMINARY AMENDMENT

December 19, 2001

Assistant Commissioner for Patents

Washington, DC 20231

Dear Sir:


Please amend the above referenced application as follows:

In the Specification:

Page 1, before line 1, insert --This application claims priority under 35 USC § 119(e)(1) of provisional application number **60/259,401** filed **12/30/00**.

| | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | |
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| 101 | 102 | 103 | 104 | 105 | 106 | 107 | 108 | 109 | 110 | 111 | 112 | 113 | 114 | 115 | 116 | 117 | 118 | 119 | 120 | 121 | 122 | 123 | 124 | 125 | 126 | 127 | 128 | 129 | 130 | 131 | 132 | 133 | 134 | 135 | 136 | 137 | 138 | 139 | 140 | 141 | 142 | 143 | 144 | 145 | 146 | 147 | 148 | 149 | 150 | 151 | 152 | 153 | 154 | 155 | 156 | 157 | 158 | 159 | 160 | 161 | 162 | 163 | 164 | 165 | 166 | 167 | 168 | 169 | 170 | 171 | 172 | 173 | 174 | 175 | 176 | 177 | 178 | 179 | 180 | 181 | 182 | 183 | 184 | 185 | 186 | 187 | 188 | 189 | 190 | 191 | 192 | 193 | 194 | 195 | 196 | 197 | 198 | 199 | 200 |
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If the Examiner has any questions or other correspondence regarding this application, Applicant requests that the Examiner contact Applicant's attorney at the below listed telephone number and address.


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